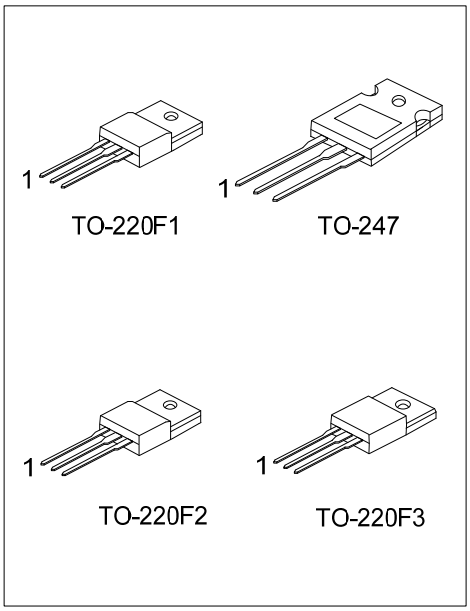
20A, 650V N-CHANNEL POWER MOSFET



■ DESCRIPTION

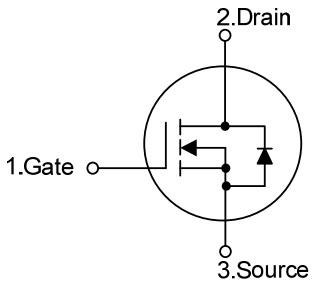
The UTC **20N65-HC** is a N-channel enhancement MOSFET using UTC's advanced technology to provide the customers with perfect $R_{DS(ON)}$, high switching speed, high current capacity and low gate charge.

The UTC **20N65-HC** is universally applied in low voltage such as automotive, high efficiency switching for AC/DC converters and DC motor control, etc.

■ FEATURES

* $R_{DS(ON)} \leq 0.4\ \Omega$ @ V_{GS}=10V, I_D=10A
* High Switching Speed

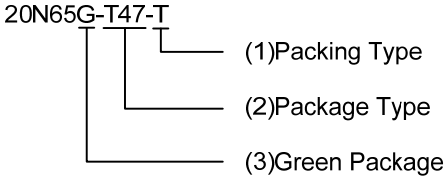
■ SYMBOL



■ ORDERING INFORMATION

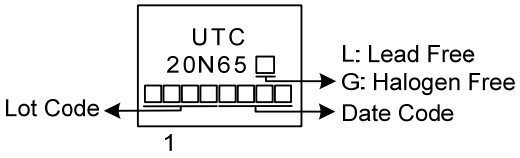
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
20N65L-TF1-T	20N65G-TF1-T	TO-220F1	G	D	S	Tube
20N65L-TF2-T	20N65G-TF2-T	TO-220F2	G	D	S	Tube
20N65L-TF3T-T	20N65G-TF3T-T	TO-220F3	G	D	S	Tube
20N65L-T47-T	20N65G-T47-T	TO-247	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source



(1) T: Tube
(2) TF1: TO-220F1, TF2: TO-220F2, TF3T: TO-220F3, T47: TO-247
(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	±30	V
Continuous Drain Current	Continuous	I_D	20	A
	Pulsed	I_{DM}	40	A
Single Pulsed Avalanche Energy (Note 3)		E_{AS}	1242	mJ
Power Dissipation	TO-220F1/TO-220F2 TO-220F3	P_D	44	W
	TO-247		320	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating : Pulse width limited by maximum junction temperature.
3. L=30mH, I_{AS}=9.1A, V_{DD}=50V, R_G=25Ω, Starting T_J = 25°C

■ THERMAL DATA

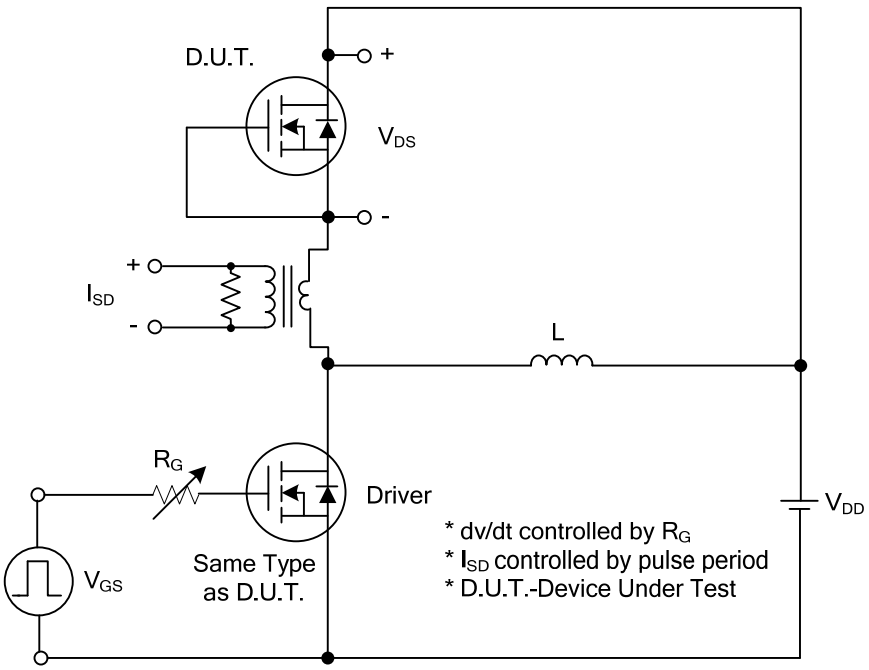
PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220F1/TO-220F2 TO-220F3	θ_{JA}	62.5	°C/W
	TO-247		40	°C/W
Junction to Case	TO-220F1/TO-220F2 TO-220F3	θ_{JC}	2.84	°C/W
	TO-247		0.39	°C/W

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

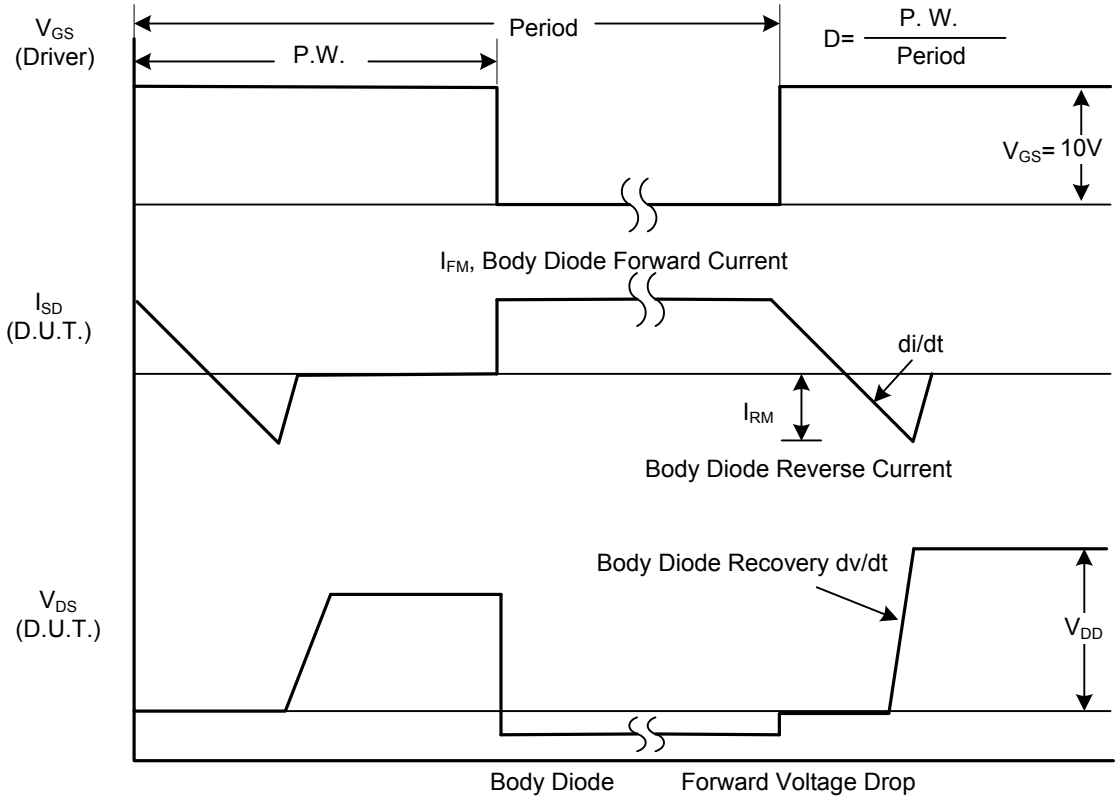
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D=250μA, V_{GS}=0V	650			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=650V, V_{GS}=0V			10	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS}=+30V, V_{DS}=0V			+100	nA
	Reverse		V_{GS}=-30V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=10A			0.4	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		3320		pF
Output Capacitance		C_{OSS}			300		pF
Reverse Transfer Capacitance		C_{RSS}			22		pF
SWITCHING PARAMETERS							
Total Gate Charge		Q_G	V_{DS}=400V, V_{GS}=10V, I_D=20A I_G=1mA (Note 1, 2)		80		nC
Gate to Source Charge		Q_{GS}			22		nC
Gate to Drain Charge		Q_{GD}			23		nC
Turn-ON Delay Time		$t_{D(ON)}$	V_{DD}=100V, V_{GS}=10V, I_D=20A, R_G=25Ω (Note 1, 2)		44		ns
Rise Time		t_R			31		ns
Turn-OFF Delay Time		$t_{D(OFF)}$			245		ns
Fall-Time		t_F			72		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S				20	A
Maximum Body-Diode Pulsed Current		I_{SM}				40	A
Drain-Source Diode Forward Voltage		V_{SD}	I_S=20A, V_{GS}=0V			1.4	V

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

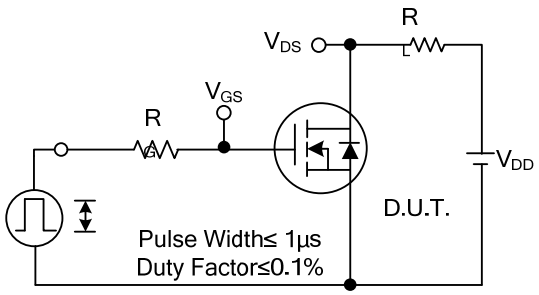


Peak Diode Recovery dv/dt Test Circuit

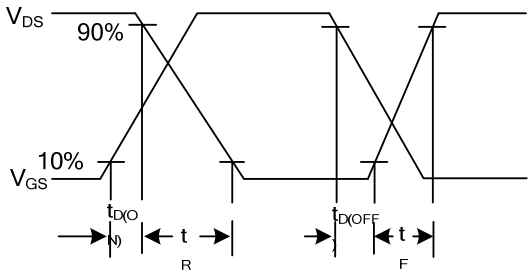


Peak Diode Recovery dv/dt Waveforms

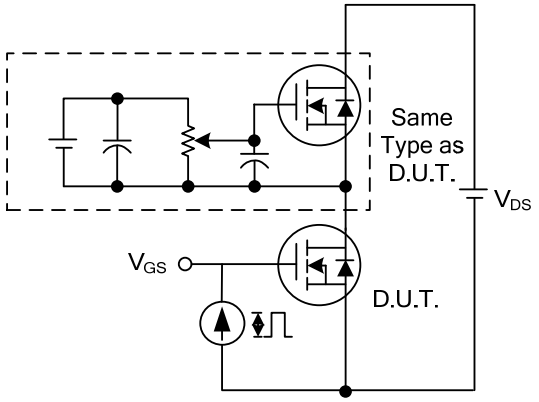
■ TEST CIRCUITS AND WAVEFORMS



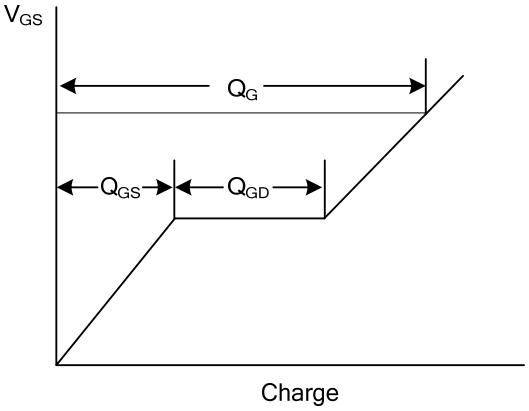
Switching Test Circuit



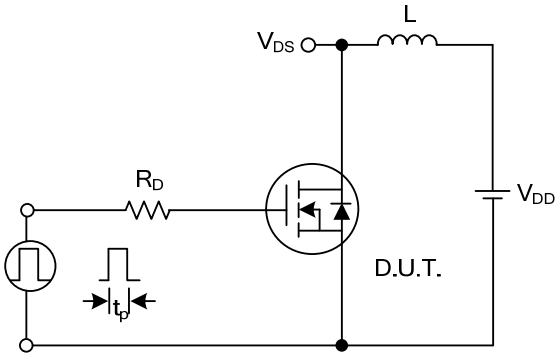
Switching Waveforms



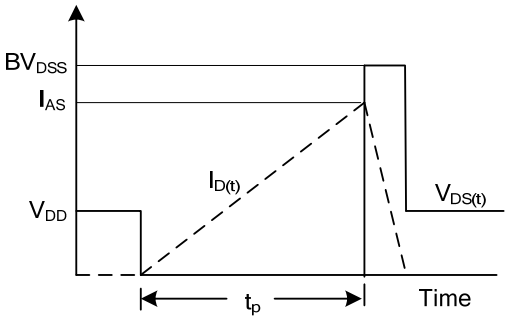
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms